

2SK4115

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 1.6 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 5.0 S$ (typ.)
- Low leakage current: $I_{DSS} = 100 \mu A$ (max) ($V_{DS} = 720 V$)
- Enhancement model: $V_{th} = 2.0 \sim 4.0 V$ ($V_{DS} = 10 V, I_D = 1 mA$)

Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	V_{DSS}	900	V	
Drain-gate voltage ($R_{GS} = 20 k\Omega$)	V_{DGR}	900	V	
Gate-source voltage	V_{GSS}	± 30	V	
Drain current	DC (Note 1)	I_D	7	A
	Pulse (Note 1)	I_{DP}	21	
Drain power dissipation ($T_c = 25^\circ C$)	P_D	150	W	
Single pulse avalanche energy (Note 2)	E_{AS}	491	mJ	
Avalanche current	I_{AR}	7	A	
Repetitive avalanche energy (Note 3)	E_{AR}	15	mJ	
Channel temperature	T_{ch}	150	$^\circ C$	
Storage temperature range	T_{stg}	$-55 \sim 150$	$^\circ C$	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.833	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	50	$^\circ C/W$

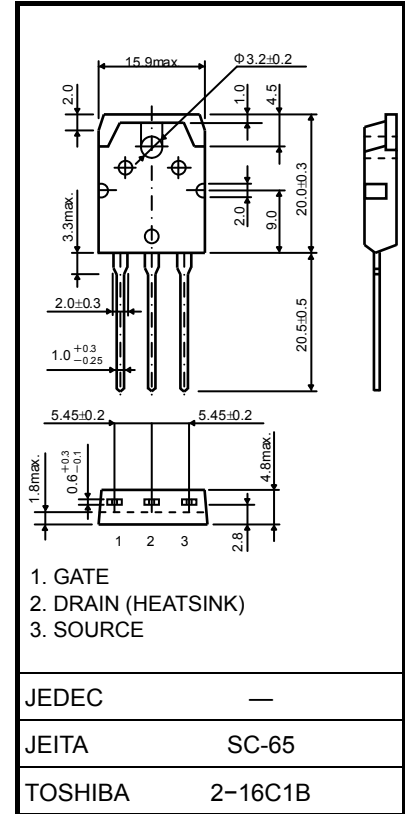
Note 1: Ensure that the channel temperature does not exceed $150^\circ C$ during use of the device.

Note 2: $V_{DD} = 90 V, T_{ch} = 25^\circ C, L = 18.4 mH, R_G = 25 \Omega, I_{AR} = 7 A$

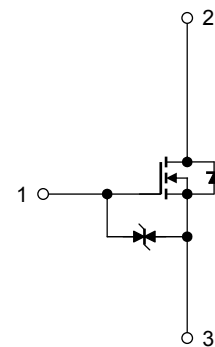
Note 3: Repetitive rating: pulse width limited by max junction temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 4.6 g (typ.)



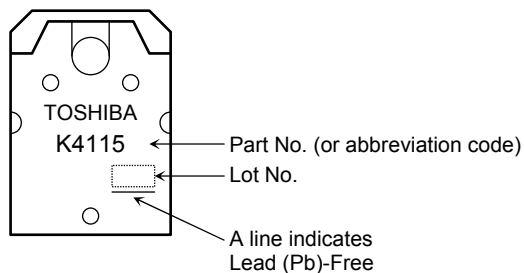
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10\ \mu\text{A}, V_{DS} = 0\text{ V}$	± 30	—	—	V
Drain cutoff current		I_{DSS}	$V_{DS} = 720\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	900	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 3.5\text{ A}$	—	1.6	2.0	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 3.5\text{ A}$	3.5	5.0	—	S
Input capacitance		C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1650	—	pF
Reverse transfer capacitance		C_{rss}		—	30	—	
Output capacitance		C_{oss}		—	140	—	
Switching time	Rise time	t_r	<p>Duty $\leq 1\%$, $t_w = 10\ \mu\text{s}$</p>	—	50	—	ns
	Turn-on time	t_{on}		—	90	—	
	Fall time	t_f		—	70	—	
	Turn-off time	t_{off}		—	240	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 7\text{ A}$	—	45	—	nC
Gate-source charge		Q_{gs}		—	24	—	
Gate-drain ("Miller") charge		Q_{gd}		—	21	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	7	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	21	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 7\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 7\text{ A}, V_{GS} = 0\text{ V},$	—	1400	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	12	—	μC

Marking



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